RoHS COMPLIANT

Vishay Semiconductors

Insulated Ultrafast Rectifier Module, 200 A



- Two fully independent diodes
- · Ceramic fully insulated package $(V_{ISOL} = 2500 V_{AC})$
- Ultrafast reverse recovery
- Ultrasoft reverse recovery current shape
- · Low forward voltage
- Optimized for power conversion: Welding and industrial SMPS applications
- · Industry standard outline
- · Plug-in compatible with other SOT-227 packages
- · Easy to assemble
- Direct mounting to heatsink
- UL approved file E78996
- Compliant to RoHS directive 2002/95/EC

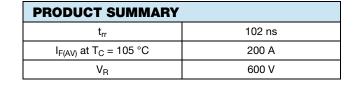
DESCRIPTION

The UFL200FA60P insulated modules integrate two state of the art Vishay Semiconductors ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The planar structure of the diodes, and the platinum doping life-time control, provide a ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, dc-to-dc converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V _R		600	V	
Continuous forward current per diode	١ _F	T _C = 85 °C	144	A	
Single pulse forward current per diode	I _{FSM}	T _C = 25 °C	1000		
Maximum power dissipation per module	PD	T _C = 85 °C	360	W	
Isolation voltage	VISOL	Any terminal to case, $t = 1 \min$	2500	V	
Operating junction and storage temperatures	T _J , T _{Stg}		- 55 to 175	°C	

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA	600	-	-	
Forward voltage		I _F = 100 A	-	1.28	1.44	V µA mA
	V	I _F = 200 A	-	1.48	1.66	
	V _{FM}	I _F = 100 A, T _J = 125 °C	-	1.13	1.24	
		I _F = 200 A	-	1.37	1.55	
Reverse leakage current		$V_{R} = V_{R}$ rated	-	5	100	μA
	I _{RM}	$T_J = 175 \text{ °C}, V_R = V_R \text{ rated}$	-	0.2	1	mA
Junction capacitance	CT	V _R = 600 V	-	80	-	pF

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 50 A V _B = 200 V	-	102	141	ns
		T _J = 125 °C		-	210	293	
Peak recovery current		T _J = 25 °C		-	9	12	•
	IRRM	T _J = 125 °C	v _R = 200 v dl _F /dt = 200 A/µs	-	21	25	A
Reverse recovery charge	0	T _J = 25 °C	2007040	-	443	744	nC
	Q _{rr}	T _J = 125 °C		-	2086	3355	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	P		-	-	0.5	°C/W
Junction to case, both leg conducting	– R _{thJC}		-	-	0.25	K/W
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.05	-	1
Weight			-	30	-	g
Mounting torque			-	1.3	-	Nm



1000

100

10

1 L

0.5

Instantaneous Forward Current - I $_{\rm F}$ (A)

UFL200FA60P

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Reverse Current - I _R (µA)

10

1

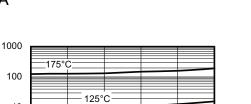
0.1

0.01

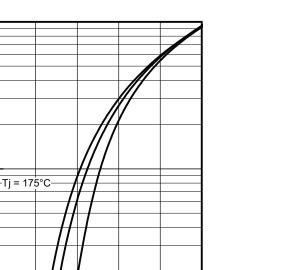
0.001 L

200

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25°C



Tj = 125°C

Tj = 25°C

1.5

Forward Voltage Drop - V_c(V)

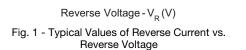
Fig. 1 - Typical Forward Voltage Drop Characteristics

(Per Diode)

2.0

2.5

1.0

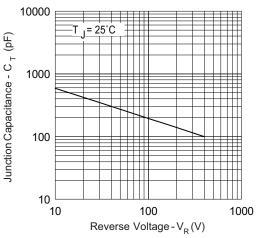


400

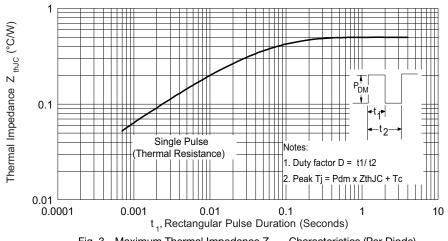
500

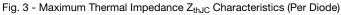
600

300









For technical questions within your region, please contact one of the following: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u>

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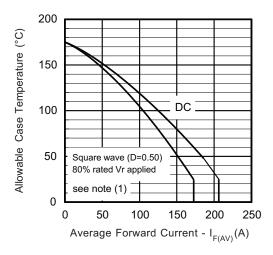


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

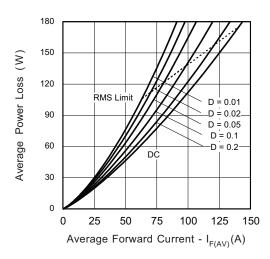


Fig. 5 - Forward Power Loss Characteristics (Per Leg)

Note

 $\begin{array}{ll} \mbox{(1)} & \mbox{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ \mbox{Pd} = \mbox{Forward power loss} = I_{F(AV)} \times V_{FM} \mbox{ at } (I_{F(AV)}/D) \mbox{ (see fig. 6); } \\ \mbox{Pd}_{REV} = \mbox{Inverse power loss} = V_{R1} \times I_R \mbox{ (1 - D); } I_R \mbox{ at } V_{R1} = 80 \ \% \mbox{ rated } V_R \end{array}$

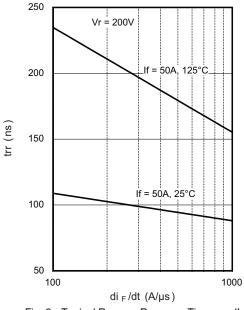
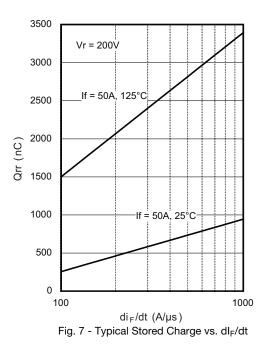


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt



Document Number: 94551 Revision: 21-Jul-10



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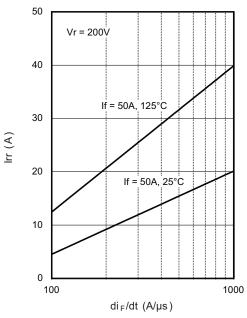


Fig. 9 - Typical Stored Current vs. dl_F/dt

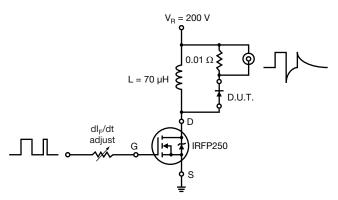
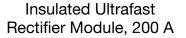
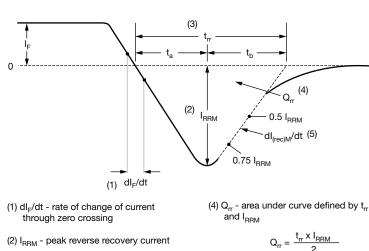


Fig. 10 - Reverse Recovery Parameter Test Circuit

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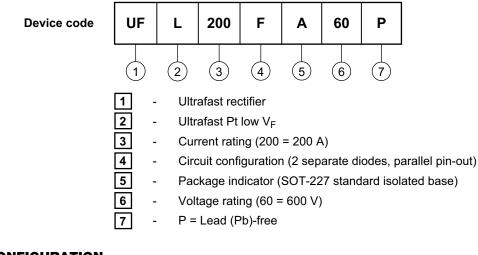
(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 $\mathrm{I}_{\mathrm{RRM}}$ and 0.50 $\mathrm{I}_{\mathrm{RRM}}$ extrapolated to zero current.

$$Q_{\rm rr} = \frac{l_{\rm rr} \times l_{\rm RRM}}{2}$$

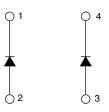
(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE



CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95036				
Packaging information	www.vishay.com/doc?95037				

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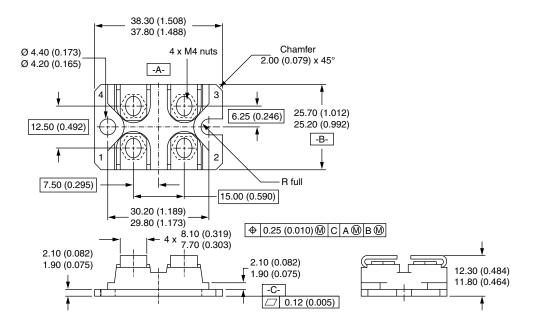


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SOT-227

DIMENSIONS in millimeters (inches)



Notes

- Dimensioning and tolerancing per ANSI Y14.5M-1982
- Controlling dimension: millimeter



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